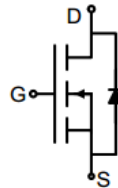
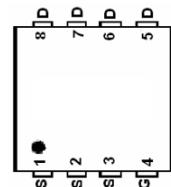
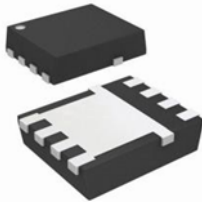


N-Channel Enhancement Mode Power MOSFET

Description The G100N03D5 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.		 Schematic diagram	
General Features • V_{DS} 30V • I_D (at $V_{GS} = 10V$) 100A • $R_{DS(ON)}$ (at $V_{GS} = 10V$) < 2.5mΩ • $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) < 3.5mΩ • 100% Avalanche Tested • RoHS Compliant		 Marking and pin assignment	
Application • Power switch • DC/DC converters		 DFN5*6-8L	
Device	Package	Marking	Packaging
G100N03D5	DFN5*6-8L	G100N03	5000pcs/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Continuous Drain Current	I_D	100	A
Pulsed Drain Current (note1)	I_{DM}	400	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	100	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

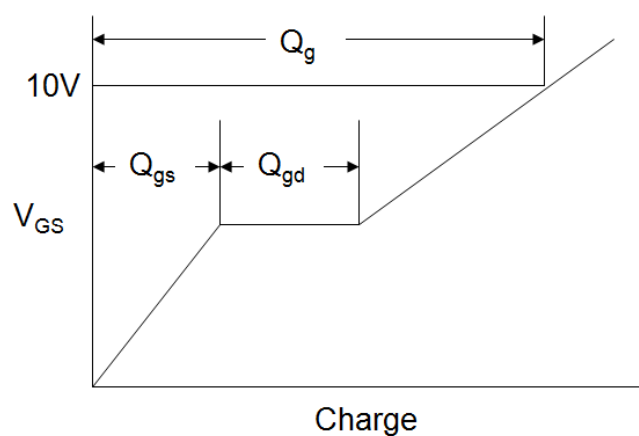
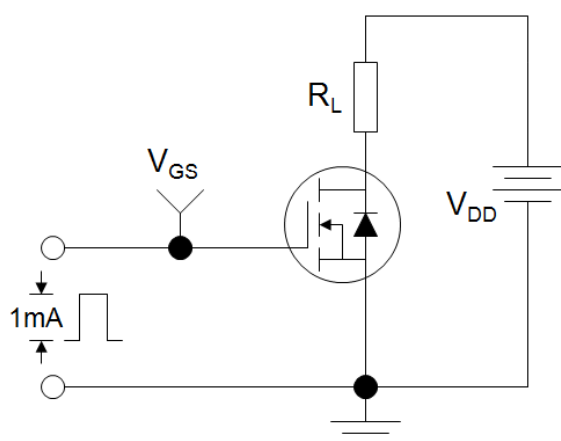
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	$^\circ\text{C/W}$

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	30	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.2	1.6	2.5	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 20A	--	2.2	2.5	mΩ
		V _{GS} = 4.5V, I _D = 10A	--	3.1	3.5	
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 15V, f = 1.0MHz	--	5000	--	pF
Output Capacitance	C _{oss}		--	1135	--	
Reverse Transfer Capacitance	C _{rss}		--	563	--	
Total Gate Charge	Q _g	V _{DD} = 15V, I _D = 20A, V _{GS} = 10V	--	38	--	nC
Gate-Source Charge	Q _{gs}		--	9	--	
Gate-Drain Charge	Q _{gd}		--	13	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 15V, I _D = 20A, R _G = 2.5Ω	--	26	--	ns
Turn-on Rise Time	t _r		--	24	--	
Turn-off Delay Time	t _{d(off)}		--	91	--	
Turn-off Fall Time	t _f		--	39	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	100	A
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 10A, V _{GS} = 0V	--	--	1.2	V

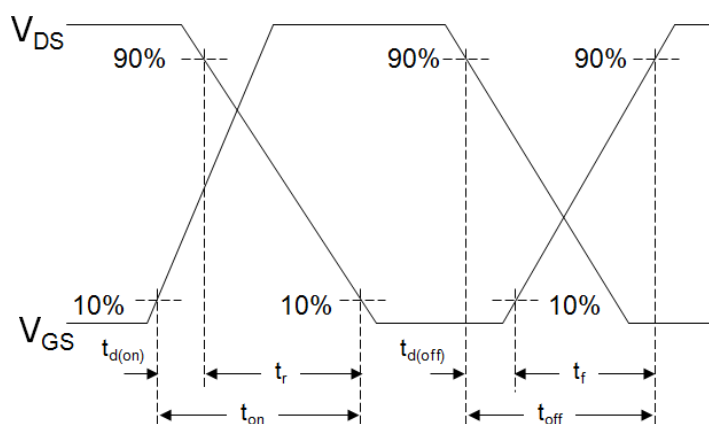
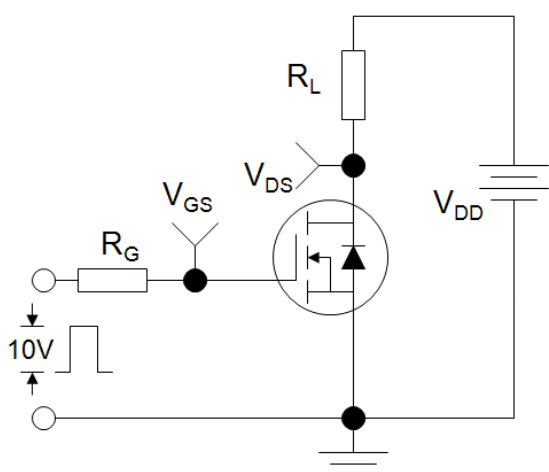
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G

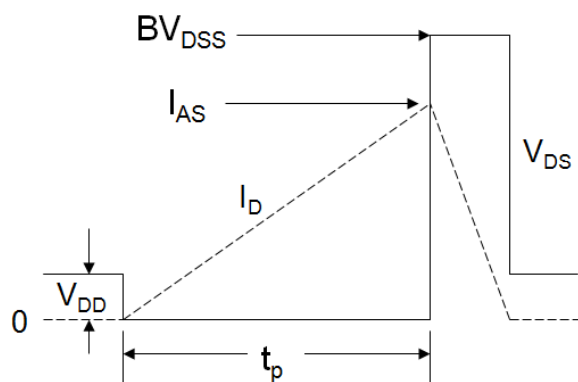
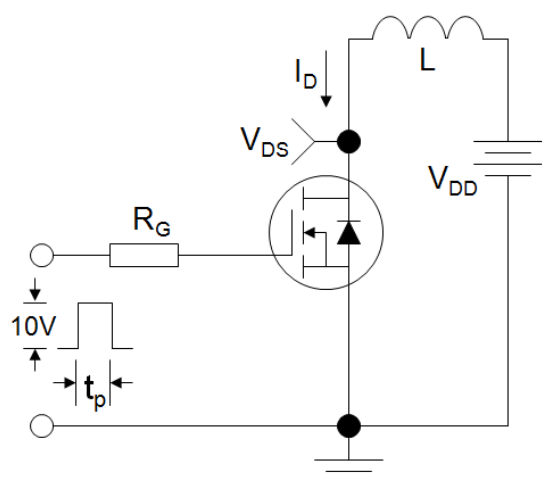
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

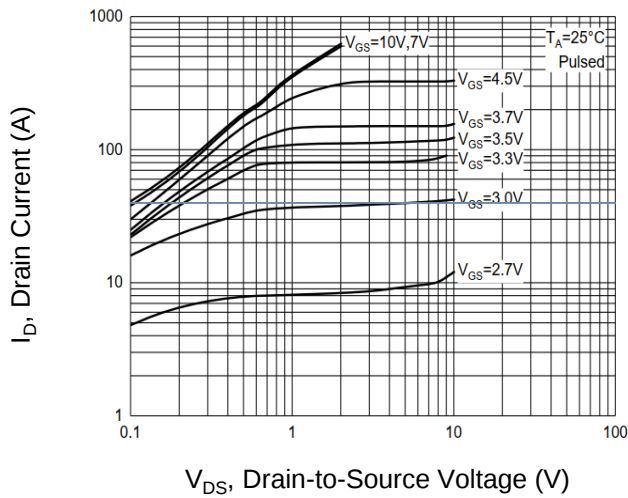


Figure 2. Transfer Characteristics

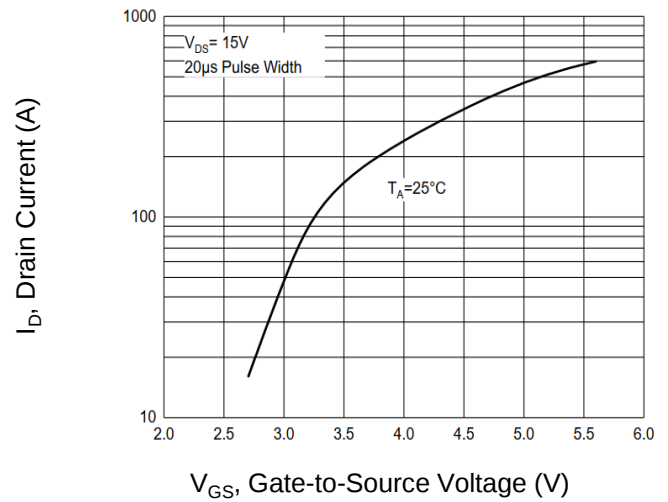


Figure 3. Threshold Voltage

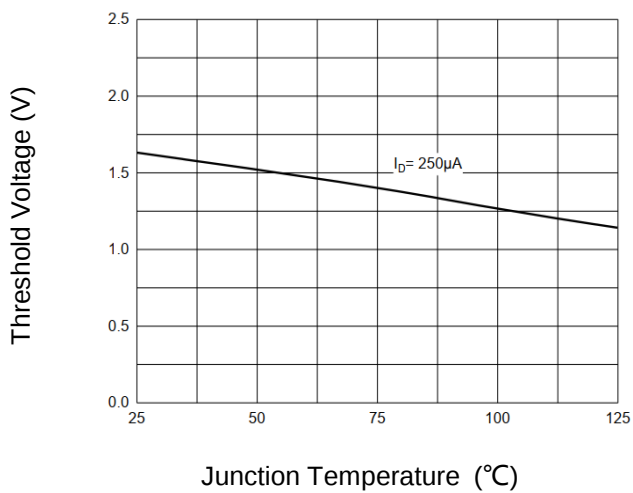


Figure 4. Drain Source On Resistance

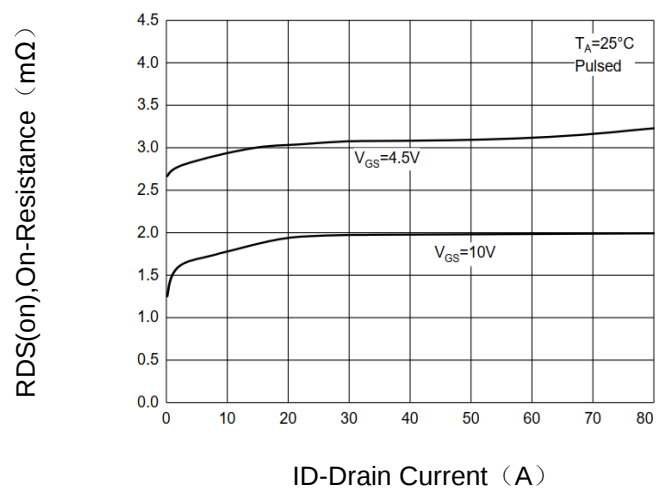


Figure 5. $R_{DS(on)} - V_{GS}$

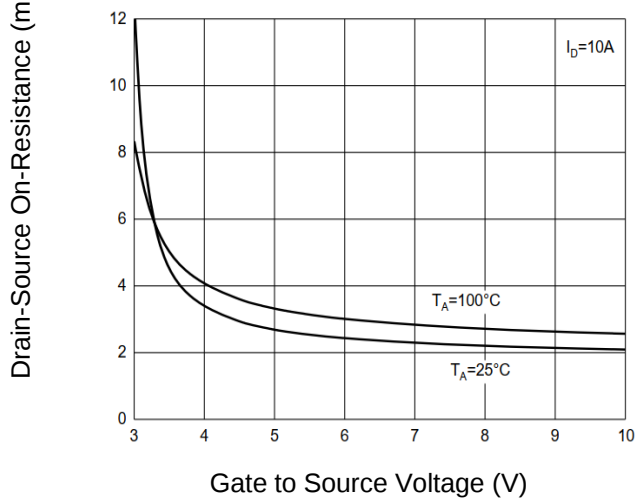
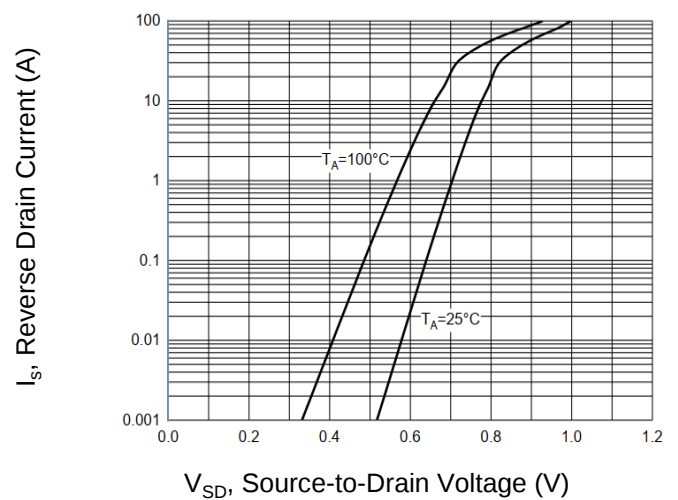
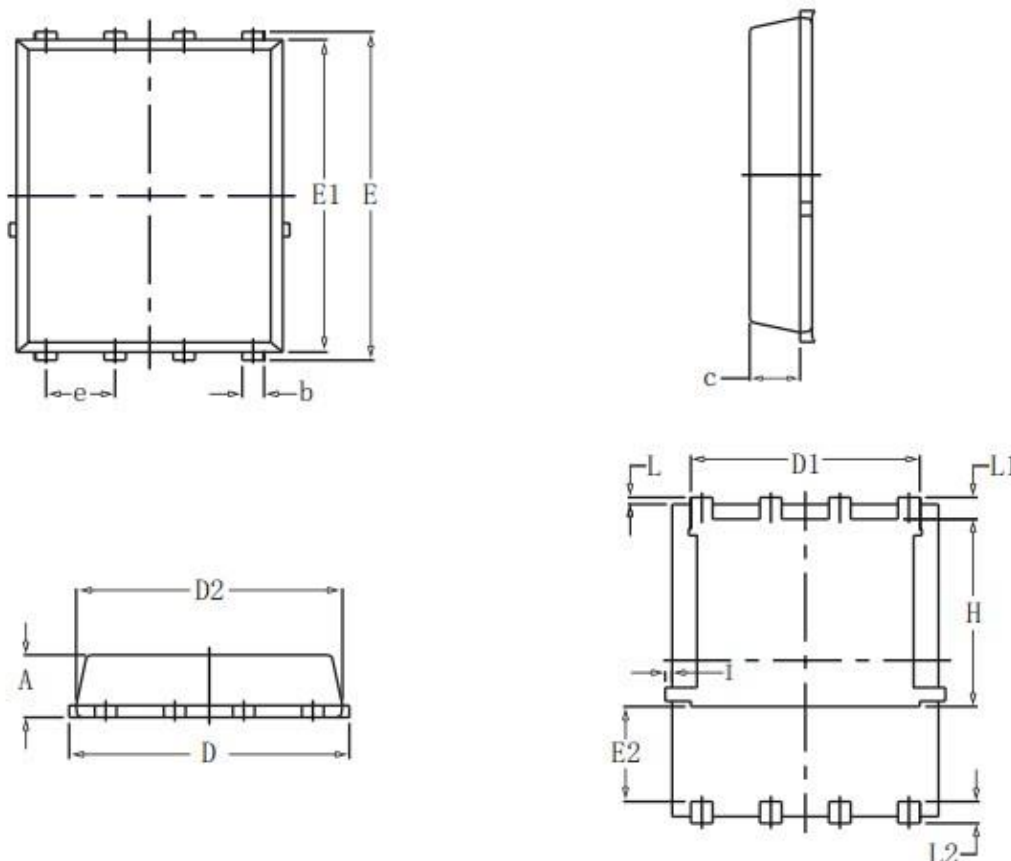


Figure 6. Source-Drain Diode Forward



DFN5*6-8L Package Information



SYMBOL	COMMON			
	MM		INCH	
	MIN	MAX	MIN	MAX
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.970	0.0324	0.0382
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.59	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	-	0.0630	-
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	-	0.18	-	0.0070